

# Product Change Notification - SYST-03NAPO573

#### Date:

06 Mar 2020

# Product Category:

Linear Comparators

### Affected CPNs:

**7** 

### Notification subject:

Data Sheet - MCP6566/7/9 Data Sheet

#### Notification text:

SYST-03NAPO573 Microchip has released a new Product Documents for the MCP6566/7/9 Data Sheet of devices. If you are using one of these devices please read the document located at <u>MCP6566/7/9 Data Sheet</u>.

# Notification Status: Final

# **Description of Change:**

The following is the list of modifications: 1. Updated package drawings for the 5-Lead SC70 and 14-lead TSSOP packages in Section 6.0 &Idquo;Packaging Information".

### Impacts to Data Sheet: None

Reason for Change: To Improve Manufacturability

Change Implementation Status: Complete

### Date Document Changes Effective: 06 Mar 2020

**NOTE:** Please be advised that this is a change to the document only the product has not been changed.

# Markings to Distinguish Revised from Unrevised Devices: N/A

#### Attachment(s):

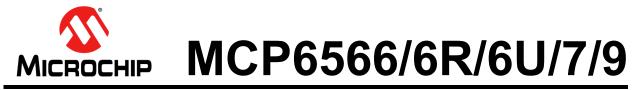
MCP6566/7/9 Data Sheet

Please contact your local <u>Microchip sales office</u> with questions or concerns regarding this notification.

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MCP6566T-E/LT MCP6566T-E/LTV02 MCP6566T-E/LTVAO MCP6566T-E/OT MCP6566RT-E/OT MCP6566UT-E/OT MCP6566UT-E/OT MCP6566UT-E/OTV01 MCP6566T-E/OTVAO MCP6566UT-E/OTVAO MCP6566RT-E/OT MCP6566UT-E/OT MCP6566UT-E/OT MCP6566UT-E/OTV01 MCP6566UT-E/OTVAO MCP6567-E/MS MCP6567-E/MSVAO MCP6567-E/SN MCP6567T-E/MS MCP6567T-E/MSVAO MCP6567T-E/SN MCP6569-E/SL MCP6569-E/ST MCP6569-E/STVAO MCP6569T-E/SL MCP6569T-E/ST MCP6569T-E/STVAO



# **1.8V Low-Power Open-Drain Output Comparator**

#### Features

- Propagation Delay at 1.8  $V_{\mbox{\scriptsize DD}}$ :
- 56 ns (typical) high-to-low
- Low Quiescent Current: 100 μA (typical)
- Input Offset Voltage: ±3 mV (typical)
- Rail-to-Rail Input:  $V_{SS} 0.3V$  to  $V_{DD} + 0.3V$
- Open-Drain Output
- Wide Supply Voltage Range: 1.8V to 5.5V
- Available in Single, Dual and Quad
- Packages: SC70, SOT-23, SOIC, MSOP, TSSOP

#### **Typical Applications**

- Laptop Computers
- Mobile Phones
- Handheld Electronics
- RC Timers
- Alarm and Monitoring Circuits
- Window Comparators
- Multivibrators

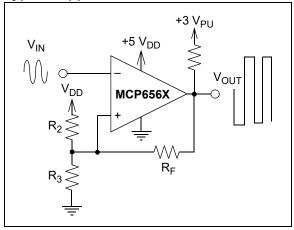
#### **Design Aids**

- Microchip Advanced Part Selector (MAPS)
- Analog Demonstration and Evaluation Boards
- Application Notes
- SPICE Macro Model

#### **Related Device**

Push-Pull Output: MCP6561/1R/1U/2/4

#### **Typical Application Circuit**



#### Description

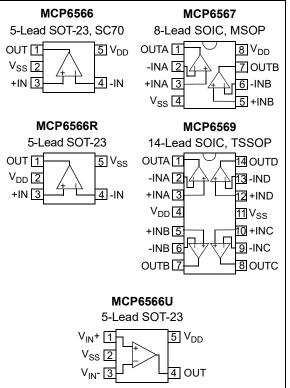
The Microchip MCP6566/6R/6U/7/9 family of opendrain output comparators is offered in single, dual and quad configurations.

These comparators are optimized for low-power 1.8V, single-supply applications with greater than rail-to-rail input operation. The internal input hysteresis eliminates output switching due to internal input noise voltage, reducing current draw.

The open-drain output of the MCP6566/6R/6U/7/9 family requires a pull-up resistor. It supports pull-up voltages that are above and below  $V_{DD}$ , which can be used to level shift. The output toggle frequency can reach a typical 4 MHz (typical) while limiting supply current surges and dynamic power consumption during switching.

This family operates with a single-supply voltage of 1.8V to 5.5V while drawing less than 100  $\mu$ A/comparator of quiescent current (typical).

#### Package Types



NOTES:

### 1.0 ELECTRICAL CHARACTERISTICS

#### 1.1 Absolute Maximum Ratings<sup>†</sup>

V <sub>DD</sub> – V <sub>SS</sub>	V
Open-Drain OutputV <sub>SS</sub> + 10.5	V
All Other Inputs and Outputs	V
Analog Input (V <sub>IN</sub> )†† V <sub>SS</sub> – 1.0V to V <sub>DD</sub> + 1.0V	V
Difference Input voltage $ V_{DD} - V_{SS} $	sl
Output Short-Circuit Current±25 mA	Ą
Current at Input Pins±2 mA	Ą
Current at Output and Supply Pins±50 mA	4
Storage Temperature65°C to +150°C	С
Ambient Temperature with Power Applied40°C to +125°C	С
Junction Temperature+150°C	С
ESD Protection on All Pins (HBM/MM) $\geq$ 4 kV/300V	V

 Notice: Stresses above those listed under "Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at those or any other conditions above those indicated in the operational listings of this specification is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

**††** See Section 4.1.2 "Input Voltage and Current Limits".

# DC CHARACTERISTICS

**Electrical Characteristics:** Unless otherwise indicated:  $V_{DD}$  = +1.8V to +5.5V,  $V_{SS}$  = GND,  $T_A$  = +25°C,  $V_{IN}$ + =  $V_{DD}/2$ ,  $V_{IN}$ - =  $V_{SS}$  and  $R_{PULL UP}$  = 20 k $\Omega$  to  $V_{PU}$  =  $V_{DD}$  (see Figure 1-1).

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Parameters	Symbol	Min	Тур	Мах	Units	Conditions
Power Supply						
Supply Voltage	V <sub>DD</sub>	1.8		5.5	V	
Quiescent Current per Comparator	ا <sub>Q</sub>	60	100	130	μA	I <sub>OUT</sub> = 0
Power Supply Rejection Ratio	PSRR	63	70	_	dB	$V_{CM} = V_{SS}$
Input						
Input Offset Voltage	V <sub>OS</sub>	-10	±3	+10	mV	V <sub>CM</sub> = V <sub>SS</sub> (Note 1)
Input Offset Drift	$\Delta V_{OS} / \Delta T$	—	±2	_	µV/°C	$V_{CM} = V_{SS}$
Input Offset Current	I <sub>OS</sub>	—	±1	_	pА	V <sub>CM</sub> = V <sub>SS</sub>
Input Bias Current	I <sub>B</sub>	—	1	_	pА	T <sub>A</sub> = +25°C, V <sub>IN</sub> - = V <sub>DD</sub> /2
		_	60	_	pА	T <sub>A</sub> = +85°C, V <sub>IN</sub> - = V <sub>DD</sub> /2
		_	1500	5000	pА	T <sub>A</sub> = +125°C, V <sub>IN</sub> - = V <sub>DD</sub> /2
Input Hysteresis Voltage	V <sub>HYST</sub>	1.0	_	5.0	mV	V <sub>CM</sub> = V <sub>SS</sub> (Notes 1, 2)
Input Hysteresis Linear Temp. Co.	TC <sub>1</sub>	_	10	_	µV/°C	
Input Hysteresis Quadratic Temp. Co.	TC <sub>2</sub>	_	0.3	_	µV/°C <sup>2</sup>	
Common-Mode Input Voltage Range	V <sub>CMR</sub>	$V_{SS} - 0.2$	_	V <sub>DD</sub> + 0.2	V	V <sub>DD</sub> = 1.8V
		$V_{SS} - 0.3$		V <sub>DD</sub> + 0.3	V	V <sub>DD</sub> = 5.5V
Common-Mode Rejection Ratio	CMRR	54	66	_	dB	$V_{CM}$ = -0.3V to $V_{DD}$ + 0.3V, $V_{DD}$ = 5.5V
		50	63	_	dB	$V_{CM} = V_{DD}/2$ to $V_{DD} + 0.3V$ , $V_{DD} = 5.5V$
		54	65		dB	$V_{CM}$ = -0.3V to $V_{DD}/2$ , $V_{DD}$ = 5.5V
Common-Mode Input Impedance	Z <sub>CM</sub>	_	10 <sup>13</sup>   4	_	Ω  pF	
Differential Input Impedance	Z <sub>DIFF</sub>	_	10 <sup>13</sup>   2	_	Ω  pF	

**Note 1:** The input offset voltage is the center of the input referred trip points. The input hysteresis is the difference between the input referred trip points.

2:  $V_{HYST}$  at different temperatures is estimated using  $V_{HYST}$  (T<sub>A</sub>) =  $V_{HYST}$  @ +25°C + (T<sub>A</sub> - 25°C) TC<sub>1</sub> + (T<sub>A</sub> - 25°C)<sup>2</sup> TC<sub>2</sub>.

**3:** Limit the output current to an absolute maximum rating of 50 mA.

4: The pull-up voltage for the open-drain output  $V_{PULL UP}$  can be as high as the absolute maximum rating of 10.5V. In this case,  $I_{OH leak}$  can be higher than 1  $\mu$ A (see Figure 2-30).

# **DC CHARACTERISTICS (CONTINUED)**

**Electrical Characteristics:** Unless otherwise indicated:  $V_{DD}$  = +1.8V to +5.5V,  $V_{SS}$  = GND,  $T_A$  = +25°C,  $V_{IN}$ + =  $V_{DD}/2$ ,  $V_{IN}$ - =  $V_{SS}$  and  $R_{PULL}$  UP = 20 k $\Omega$  to  $V_{PU}$  =  $V_{DD}$  (see Figure 1-1).

Parameters	Symbol	Min	Тур	Max	Units	Conditions			
Push-Pull Output									
Pull-up Voltage	V <sub>PULL_UP</sub>	1.6		5.5	V				
High-Level Output Voltage	V <sub>OH</sub>	_	_	V <sub>PULL_UP</sub>	V	See Figure 1-1 (Notes 3, 4)			
High-Level Output Current Leakage	I <sub>OH_leak</sub>	_	_	1	μA	Note 4			
Low-Level Output Voltage	V <sub>OL</sub>	_	—	0.6	V	I <sub>OUT</sub> = 3 mA/8 mA @ V <sub>DD</sub> = 1.8V/5.5V			
Short-Circuit Current (Note 3)	I <sub>SC</sub>		±30	—	mA	Not to exceed absolute max. rating			
Output Pin Capacitance	C <sub>OUT</sub>	_	8		pF				

**Note 1:** The input offset voltage is the center of the input referred trip points. The input hysteresis is the difference between the input referred trip points.

2:  $V_{HYST}$  at different temperatures is estimated using  $V_{HYST}$  (T<sub>A</sub>) =  $V_{HYST}$  @ +25°C + (T<sub>A</sub> - 25°C) TC<sub>1</sub> + (T<sub>A</sub> - 25°C)<sup>2</sup> TC<sub>2</sub>.

**3:** Limit the output current to an absolute maximum rating of 50 mA.

4: The pull-up voltage for the open-drain output  $V_{PULL UP}$  can be as high as the absolute maximum rating of 10.5V. In this case,  $I_{OH leak}$  can be higher than 1  $\mu$ A (see Figure 2-30).

# AC CHARACTERISTICS

**Electrical Characteristics:** Unless otherwise indicated:  $V_{DD}$  = +1.8V to +5.5V,  $V_{SS}$  = GND,  $T_A$  = +25°C,  $V_{IN}$ + =  $V_{DD}/2$ ,  $V_{IN}$ - =  $V_{SS}$ ,  $R_{PULL}$  UP = 20 k $\Omega$  to  $V_{PU}$  =  $V_{DD}$  and  $C_L$  = 25 pF (see Figure 1-1).

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Parameters	Symbol	Min	Тур	Max	Units	Conditions		
Propagation Delay								
High-to-Low,100 mV Overdrive	t <sub>PHL</sub>	_	56	80	ns	V <sub>CM</sub> = V <sub>DD</sub> /2, V <sub>DD</sub> = 1.8V (Note 2)		
		—	34	80	ns	$V_{CM} = V_{DD}/2, V_{DD} = 5.5V$		
Output								
Fall Time	t <sub>F</sub>	_	20		ns			
Maximum Toggle Frequency	f <sub>TG</sub>	—	4	_	MHz	V <sub>DD</sub> = 5.5V		
		_	2		MHz	V <sub>DD</sub> = 1.8V		
Input Voltage Noise	E <sub>NI</sub>	_	350		μV <sub>P-P</sub>	10 Hz to 10 MHz (Note 1)		
Nets 4. ENII is hered an ODIOE sin	1.0							

Note 1: ENI is based on SPICE simulation.

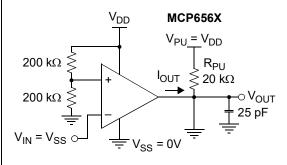
2: Rise time, t<sub>R</sub> and t<sub>PLH</sub>, depend on the load (R<sub>L</sub> and C<sub>L</sub>). These specifications are valid for the specified load only.

#### **TEMPERATURE SPECIFICATIONS**

Electrical Characteristics: Unless otherwise indicated: V <sub>DD</sub> = +1.8V to +5.5V and V <sub>SS</sub> = GND.							
Parameters	Symbol	Min	Тур	Max	Units	Conditions	
Temperature Ranges							
Specified Temperature Range	T <sub>A</sub>	-40		+125	°C		
Operating Temperature Range	T <sub>A</sub>	-40	—	+125	°C		
Storage Temperature Range	T <sub>A</sub>	-65	—	+150	°C		
Thermal Package Resistances							
Thermal Resistance, 5-Lead SC70	$\theta_{JA}$	_	331		°C/W		
Thermal Resistance, 5-Lead SOT-23	$\theta_{JA}$	_	201		°C/W		
Thermal Resistance, 8-Lead MSOP	$\theta_{JA}$	_	211		°C/W		
Thermal Resistance, 8-Lead SOIC	$\theta_{JA}$	_	149		°C/W		
Thermal Resistance, 14-Lead SOIC	$\theta_{JA}$	_	91		°C/W		
Thermal Resistance, 14-Lead TSSOP	$\theta_{JA}$	_	100		°C/W		

### 1.2 Test Circuit Configuration

This test circuit configuration is used to determine the AC and DC specifications.

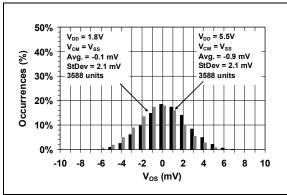


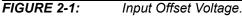
**FIGURE 1-1:** AC and DC Test Circuit for the Open-Drain Output Comparators.

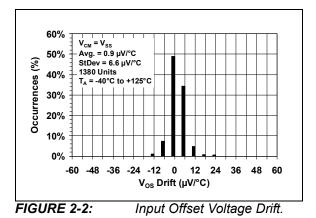
NOTES:

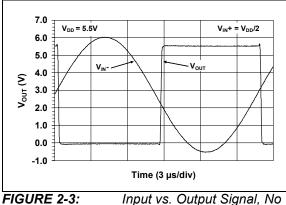
### 2.0 TYPICAL PERFORMANCE CURVES

**Note:** The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only. The performance characteristics listed herein are not tested or guaranteed. In some graphs or tables, the data presented may be outside the specified operating range (e.g., outside specified power supply range) and therefore outside the warranted range.









Phase Reversal.

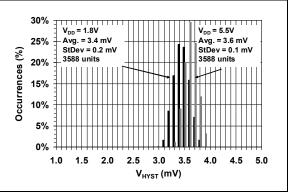
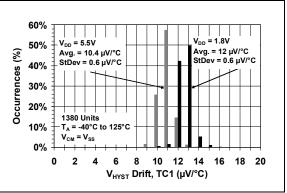
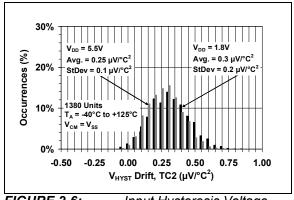


FIGURE 2-4:

Input Hysteresis Voltage.



**FIGURE 2-5:** Input Hysteresis Voltage Drift – Linear Temp. Co. (TC1).



**FIGURE 2-6:** Input Hysteresis Voltage Drift – Quadratic Temp. Co. (TC2).

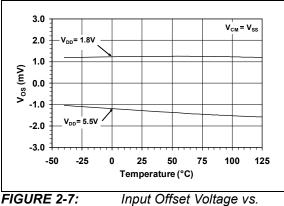


FIGURE 2-7: Temperature.

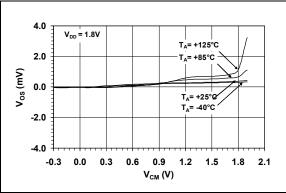


FIGURE 2-8: Input Offset Voltage vs. Common-Mode Input Voltage.

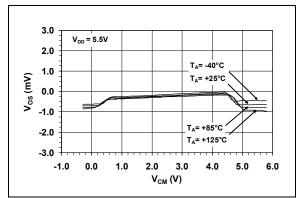
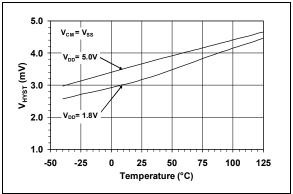
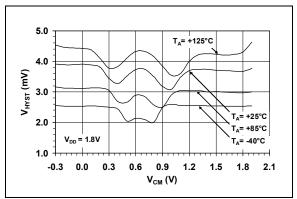


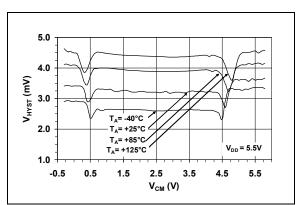
FIGURE 2-9: Input Offset Voltage vs. Common-Mode Input Voltage.



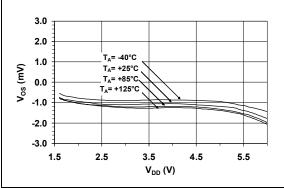
**FIGURE 2-10:** Input Hysteresis Voltage vs. Temperature.



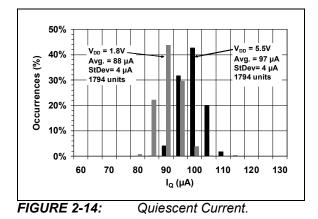
**FIGURE 2-11:** Input Hysteresis Voltage vs. Common-Mode Input Voltage.



**FIGURE 2-12:** Input Hysteresis Voltage vs. Common-Mode Input Voltage.



**FIGURE 2-13:** Input Offset Voltage vs. Supply Voltage vs. Temperature.



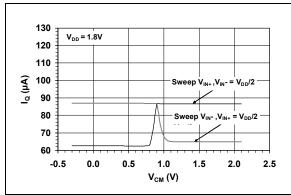
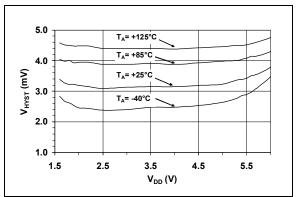
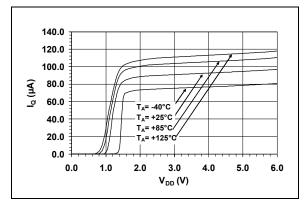


FIGURE 2-15: Quiescent Current vs. Common-mode Input Voltage.



**FIGURE 2-16:** Input Hysteresis Voltage vs. Supply Voltage vs. Temperature.



**FIGURE 2-17:** Quiescent Current vs. Supply Voltage vs. Temperature.

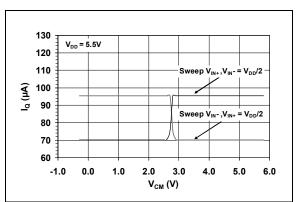


FIGURE 2-18: Quiescent Current vs. Common-mode Input Voltage.

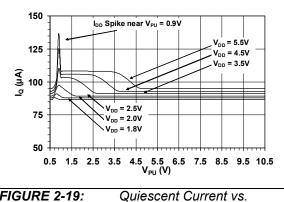


FIGURE 2-19: Pull-up Voltage.

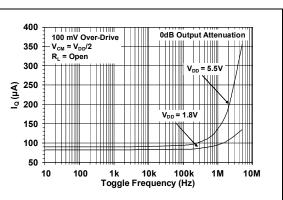


FIGURE 2-20: Quiescent Current vs. Toggle Frequency.

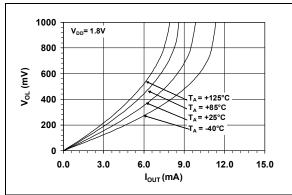


FIGURE 2-21: Output Headroom vs. Output Current.

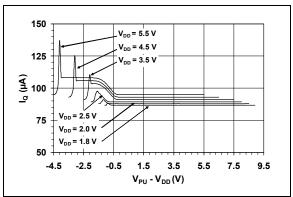
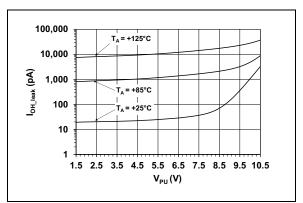
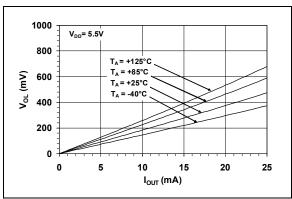


FIGURE 2-22: Quiescent Current vs. Pull-up to Supply Voltage Difference.



**FIGURE 2-23:** Output Leakage Current vs. Pull-up Voltage.



*FIGURE 2-24:* Output Headroom vs. Output Current.

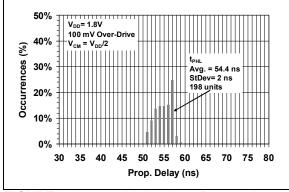


FIGURE 2-25: High-to-Low Propagation Delays.

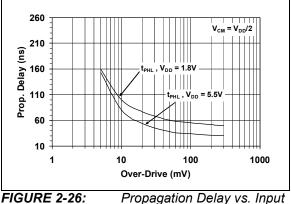


FIGURE 2-26: Propagation De Overdrive.

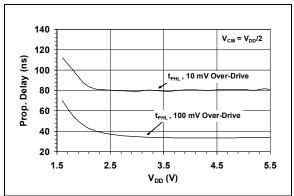
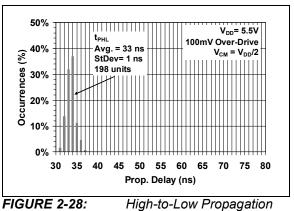
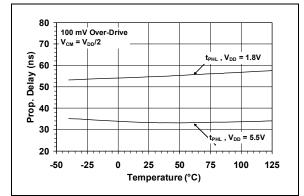


FIGURE 2-27: Propagation Delay vs. Supply Voltage.

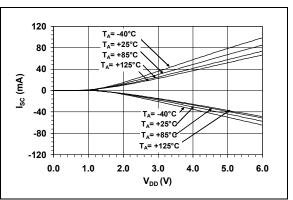


Delays.

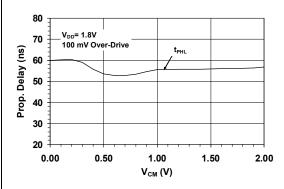
Hign-to-Low Propagatio



**FIGURE 2-29:** Propagation Delay vs. Temperature.



**FIGURE 2-30:** Short-Circuit Current vs. Supply Voltage vs. Temperature.



**FIGURE 2-31:** Propagation Delay vs. Common-Mode Input Voltage.

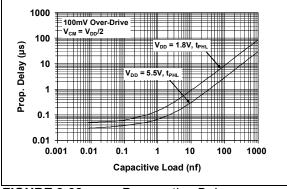


FIGURE 2-32: Propagation Delay vs. Capacitive Load.

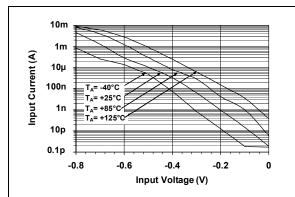
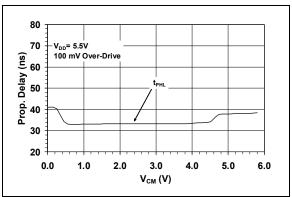
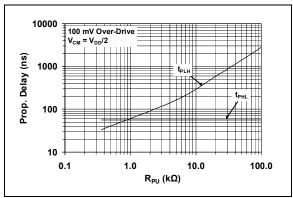


FIGURE 2-33: Input Bias Current vs. Input Voltage vs. Temperature.



**FIGURE 2-34:** Propagation Delay vs. Common-Mode Input Voltage.



*FIGURE 2-35:* Propagation Delay vs. Pull-up Resistor.

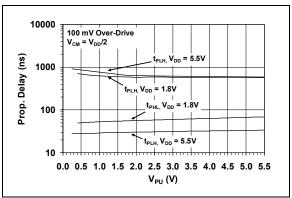
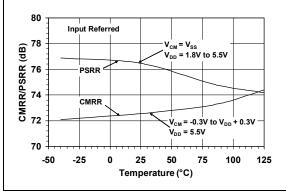
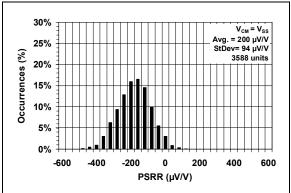


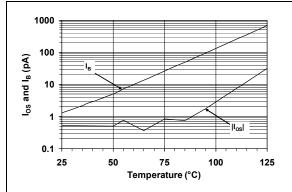
FIGURE 2-36:Propagation Delay vs.Pull-up Voltage.



**FIGURE 2-37:** Common-Mode Rejection Ratio and Power Supply Rejection Ratio vs. Temperature.



**FIGURE 2-38:** Power Supply Rejection Ratio (PSRR).



**FIGURE 2-39:** Input Offset Current and Input Bias Current vs. Temperature.

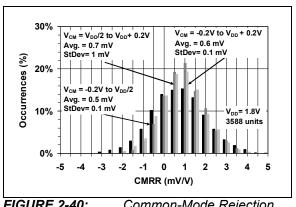


FIGURE 2-40: Ratio (CMRR).

Common-Mode Rejection

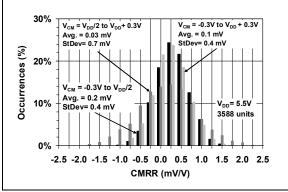
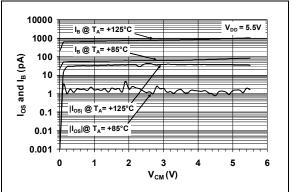


FIGURE 2-41: Common-Mode Rejection Ratio (CMRR).



**FIGURE 2-42:** Input Offset Current and Input Bias Current vs. Common-Mode Input Voltage vs. Temperature.

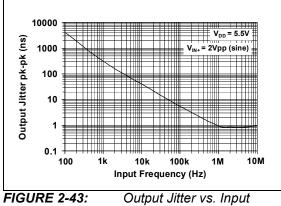


FIGURE 2-43: Frequency.

### 3.0 PIN DESCRIPTIONS

Descriptions of the pins are listed in Table 3-1.

MCP6566	MCP6566R	MCP6566U	MCP6567	MCP6569		
SC70, SOT-23	SOT-23	SOT-23	MSOP, SOIC	SOIC, TSSOP	Symbol	Description
1	1	4	1	1	OUT, OUTA	Digital Output (Comparator A)
4	4	3	2	2	V <sub>IN</sub> -, V <sub>INA</sub> -	Inverting Input (Comparator A)
3	3	1	3	3	V <sub>IN</sub> +, V <sub>INA</sub> +	Noninverting Input (Comparator A)
5	2	5	8	4	V <sub>DD</sub>	Positive Power Supply
—	—		5	5	V <sub>INB</sub> +	Noninverting Input (Comparator B)
—	—		6	6	V <sub>INB</sub> -	Inverting Input (Comparator B)
—	_		7	7	OUTB	Digital Output (Comparator B)
—	—		—	8	OUTC	Digital Output (Comparator C)
—	—		—	9	V <sub>INC</sub> -	Inverting Input (Comparator C)
—	_		—	10	V <sub>INC</sub> +	Noninverting Input (Comparator C)
2	5	2	4	11	V <sub>SS</sub>	Negative Power Supply
_	_		_	12	V <sub>IND</sub> +	Noninverting Input (Comparator D)
_	—	_	_	13	V <sub>IND</sub> -	Inverting Input (Comparator D)
_	—	_	—	14	OUTD	Digital Output (Comparator D)

TABLE 3-1: PIN FUNCTION TABLE

#### 3.1 Analog Inputs

The comparator noninverting and inverting inputs are high-impedance CMOS inputs with low bias currents.

#### 3.2 Digital Outputs

The comparator outputs are CMOS, open-drain digital outputs. They are designed to make level shifting and wired-OR easy to implement.

# 3.3 Power Supply (V<sub>SS</sub> and V<sub>DD</sub>)

The positive power supply pin ( $V_{DD}$ ) is 1.8V to 5.5V higher than the negative power supply pin ( $V_{SS}$ ). For normal operation, the other pins are at voltages between  $V_{SS}$  and  $V_{DD}$ .

Typically, these parts are used in a single (positive) supply configuration. In this case,  $V_{SS}$  is connected to ground and  $V_{DD}$  is connected to the supply.  $V_{DD}$  will need a local bypass capacitor (typically 0.01  $\mu$ F to 0.1  $\mu$ F) within 2 mm of the  $V_{DD}$  pin. These pins can share a bulk capacitor with nearby analog parts (within 100 mm), but it is not required.

NOTES:

#### 4.0 APPLICATION INFORMATION

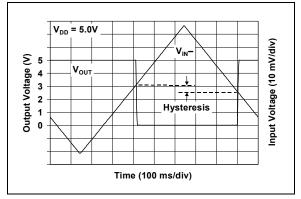
The MCP6566/6R/6U/7/9 family of open-drain output comparators is fabricated on Microchip's state-of-the-art CMOS process. They are suitable for a wide range of high-speed applications requiring low-power consumption.

#### 4.1 Comparator Inputs

#### 4.1.1 NORMAL OPERATION

The input stage of this family of devices uses two different input stages in parallel. This configuration provides three regions of operation; one operates at low input voltages, one at high input voltages, and one at mid input voltage. With this topology, the input voltage range is 0.3V above V<sub>DD</sub> and 0.3V below V<sub>SS</sub>, while providing low offset voltage throughout the Common-mode range. The input offset voltage is measured at both V<sub>SS</sub> – 0.3V and V<sub>DD</sub> + 0.3V to ensure proper operation.

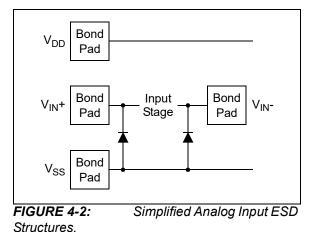
The MCP6566/6R/6U/7/9 family has an internally set hysteresis, V<sub>HYST</sub>, which is small enough to maintain input offset accuracy and large enough to eliminate output chattering caused by the comparator's own input noise voltage,  $E_{NI}$ . Figure 4-1 depicts this behavior. Input offset voltage (V<sub>OS</sub>) is the center (average) of the (input referred) low-high and high-low trip points. Input hysteresis voltage (V<sub>HYST</sub>) is the difference between the same trip points.



**FIGURE 4-1:** The MCP6566/6R/6U/7/9 Comparators' Internal Hysteresis Eliminates Output Chatter Caused by Input Noise Voltage.

#### 4.1.2 INPUT VOLTAGE AND CURRENT LIMITS

The ESD protection on the inputs can be depicted as shown in Figure 4-2. This structure was chosen to protect the input transistors and to minimize input bias current ( $I_B$ ). The input ESD diodes clamp the inputs when they try to go more than one diode drop below  $V_{SS}$ . They also clamp any voltages that go too far above  $V_{DD}$ . The diodes' breakdown voltage is high enough to allow normal operation, but low enough to bypass ESD events within the specified limits.



In order to prevent damage and/or improper operation of these amplifiers, the circuits they are in must limit the currents (and voltages) at the V<sub>IN</sub>+ and V<sub>IN</sub>- pins (see **Section 1.1 "Absolute Maximum Ratings**†" at the beginning of **Section 1.0 "Electrical Characteristics**"). Figure 4-3 shows the recommended approach to protecting these inputs. The internal ESD diodes prevent the input pins (V<sub>IN</sub>+ and V<sub>IN</sub>-) from going too far below ground, and the resistors, R<sub>1</sub> and R<sub>2</sub>, limit the possible current drawn out of the input pin. Diodes, D<sub>1</sub> and D<sub>2</sub>, prevent the input pin (V<sub>IN</sub>+ and V<sub>IN</sub>-) from going too far above V<sub>DD</sub>. When implemented as shown, resistors, R<sub>1</sub> and R<sub>2</sub>, also limit the current through D<sub>1</sub> and D<sub>2</sub>.

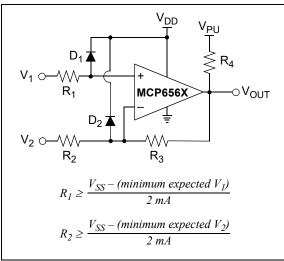


FIGURE 4-3: Protecting the Analog Inputs.

It is also possible to connect the diodes to the left of the resistors, R<sub>1</sub> and R<sub>2</sub>. In this case, the currents through the diodes, D<sub>1</sub> and D<sub>2</sub>, need to be limited by some other mechanism. The resistor then serves as an inrush current limiter; the DC current into the input pins (V<sub>IN</sub>+ and V<sub>IN</sub>-) should be very small.

A significant amount of current can flow out of the inputs when the Common-mode voltage ( $V_{CM}$ ) is below ground ( $V_{SS}$ ); see Figure 4-3. Applications that are high-impedance may need to limit the usable voltage range.

#### 4.1.3 PHASE REVERSAL

The MCP6566/6R/6U/7/9 comparator family uses CMOS transistors at the input. They are designed to prevent phase inversion when the input pins exceed the supply voltages. Figure 2-3 shows an input voltage exceeding both supplies with no resulting phase inversion.

#### 4.2 Open-Drain Output

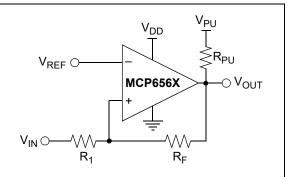
The open-drain output is designed to make level shifting and wired-OR logic easy to implement. The output stage minimizes switching current (shoot-through current from supply-to-supply) when the output changes state. See Figures 2-15, 2-18, 2-35 and 2-36 for more information.

#### 4.3 Externally Set Hysteresis

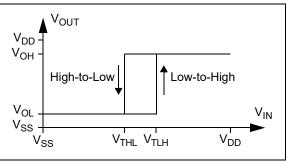
Greater flexibility in selecting hysteresis (or input trip points) is achieved by using external resistors. Hysteresis reduces output chattering when one input is slowly moving past the other. It also helps in systems in which it is best not to cycle between high and low states too frequently (e.g., air conditioner thermostatic control). Output chatter also increases the dynamic supply current.

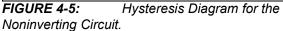
#### 4.3.1 NONINVERTING CIRCUIT

Figure 4-4 shows a noninverting circuit for singlesupply applications using just two resistors. The resulting hysteresis diagram is shown in Figure 4-5.



**FIGURE 4-4:** Noninverting Circuit with Hysteresis for Single Supply.





The trip points for Figures 4-4 and 4-5 are:

#### **EQUATION 4-1:**

$$V_{TLH} = V_{REF} \left( I + \frac{R_I}{R_F} \right) - V_{OL} \left( \frac{R_I}{R_F} \right)$$
$$V_{THL} = V_{REF} \left( I + \frac{R_I}{R_F} \right) - V_{OH} \left( \frac{R_I}{R_F} \right)$$

Where:

 $V_{TLH}$  = Trip Voltage from Low-to-High  $V_{THL}$  = Trip Voltage from High-to-Low

#### 4.3.2 INVERTING CIRCUIT

Figure 4-6 shows an inverting circuit for single supply using three resistors. The resulting hysteresis diagram is shown in Figure 4-7.

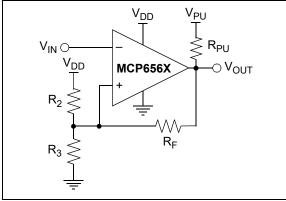
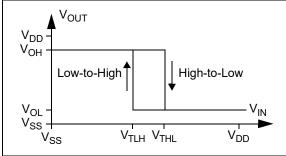


FIGURE 4-6: Hysteresis.

Inverting Circuit with



**FIGURE 4-7:** Hysteresis Diagram for the Inverting Circuit.

In order to determine the trip voltages ( $V_{THL}$  and  $V_{TLH}$ ) for the circuit shown in Figure 4-6,  $R_2$  and  $R_3$  can be simplified to the Thevenin equivalent circuit with respect to  $V_{DD}$ , as shown in Figure 4-8.

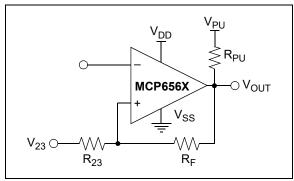


FIGURE 4-8:

Thevenin Equivalent Circuit.

Where:

$$R_{23} = \frac{R_2 R_3}{R_2 + R_3}$$
$$V_{23} = \frac{R_3}{R_2 + R_3} \times V_{DD}$$

Using this simplified circuit, the trip voltage can be calculated using the following equation:

#### **EQUATION 4-2:**

$$V_{THL} = V_{OH} \left( \frac{R_{23}}{R_{23} + R_F} \right) + V_{23} \left( \frac{R_F}{R_{23} + R_F} \right)$$
$$V_{TLH} = V_{OL} \left( \frac{R_{23}}{R_{23} + R_F} \right) + V_{23} \left( \frac{R_F}{R_{23} + R_F} \right)$$

Where:

 $V_{TLH}$  = Trip Voltage from Low-to-High  $V_{THL}$  = Trip Voltage from High-to-Low

Figure 2-21 and Figure 2-24 can be used to determine typical values for  $V_{OH}$  and  $V_{OL}.$ 

#### 4.4 Bypass Capacitors

With this family of comparators, the power supply pin (V<sub>DD</sub> for single supply) should have a local bypass capacitor (i.e., 0.01  $\mu$ F to 0.1  $\mu$ F) within 2 mm for good edge rate performance.

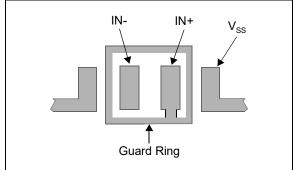
#### 4.5 Capacitive Loads

Reasonable capacitive loads (e.g., logic gates) have little impact on propagation delay (see Figure 2-32). The supply current increases with increasing toggle frequency (Figure 2-20), especially with higher capacitive loads. The output slew rate and propagation delay performance will be reduced with higher capacitive loads.

#### 4.6 PCB Surface Leakage

In applications where low input bias current is critical, PCB (Printed Circuit Board) surface leakage effects need to be considered. Surface leakage is caused by humidity, dust or other contamination on the board. Under low humidity conditions, a typical resistance between nearby traces is  $10^{12}\Omega$ . A 5V difference would cause 5 pA of current to flow. This is greater than the MCP6566/6R/6U/7/9 family's bias current at +25°C (1 pA, typical).

The easiest way to reduce surface leakage is to use a guard ring around sensitive pins (or traces). The guard ring is biased at the same voltage as the sensitive pin. An example of this type of layout is shown in Figure 4-9.

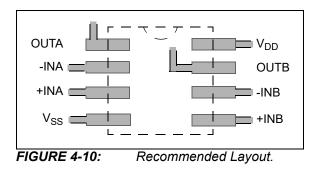


**FIGURE 4-9:** Example Guard Ring Layout for Inverting Circuit.

- 1. Inverting Configuration (Figures 4-6 and 4-9):
  - a) Connect the guard ring to the noninverting input pin (V<sub>IN</sub>+). This biases the guard ring to the same reference voltage as the comparator (e.g., V<sub>DD</sub>/2 or ground).
  - b) Connect the inverting pin ( $V_{IN}$ -) to the input pad without touching the guard ring.
- 2. Noninverting Configuration (Figure 4-4):
  - a) Connect the noninverting pin ( $V_{IN}$ +) to the input pad without touching the guard ring.
  - b) Connect the guard ring to the inverting input pin (V\_{IN}-).

#### 4.7 PCB Layout Technique

When designing the PCB layout, it is critical to note that analog and digital signal traces are adequately separated to prevent signal coupling. If the comparator output trace is at close proximity to the input traces, then large output voltage changes, from  $V_{SS}$  to  $V_{DD}$  or visa versa, may couple to the inputs and cause the device output to oscillate. To prevent such oscillation, the output traces must be routed away from the input pins. The SC70 and SOT-23 are relatively immune because the output pin OUT (Pin 1) is separated by the power pin  $V_{DD}/V_{SS}$  (Pin 2) from the input pin +IN (as long as the analog and digital traces remain separated throughout the PCB). However, the pinouts for the dual and quad packages (SOIC, MSOP, TSSOP) have OUT and -IN pins (Pins 1 and 2) close to each other. The recommended layout for these packages is shown in Figure 4-10.



#### 4.8 Unused Comparators

An unused amplifier in a quad package (MCP6569) should be configured as shown in Figure 4-11. This circuit prevents the output from toggling and causing crosstalk. It uses the minimum number of components and draws minimal current (see Figure 2-14 and Figure 2-15).

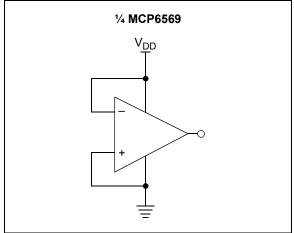
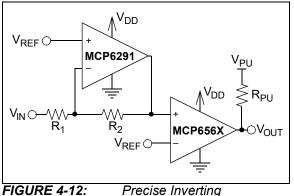


FIGURE 4-11: Unused Comparators.

#### 4.9 Typical Applications

#### 4.9.1 PRECISE COMPARATOR

Some applications require higher DC precision. An easy way to solve this problem is to use an amplifier (such as the MCP6291) to gain-up the input signal before it reaches the comparator. Figure 4-12 shows an example of this approach.



Comparator.

#### 4.9.2 WINDOWED COMPARATOR

Figure 4-13 shows one approach to designing a windowed comparator. The AND gate produces a logic '1' when the input voltage is between  $V_{RB}$  and  $V_{RT}$  (where  $V_{RT} > V_{RB}$ ).

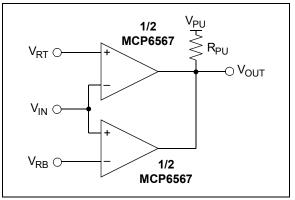


FIGURE 4-13: W

Windowed Comparator.

#### 4.9.3 BISTABLE MULTIVIBRATOR

A simple bistable multivibrator design is shown in Figure 4-14. V<sub>REF</sub> needs to be between the power supplies (V<sub>SS</sub> = GND and V<sub>DD</sub>) to achieve oscillation. The output duty cycle changes with V<sub>REF</sub>.

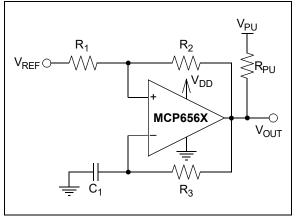


FIGURE 4-14: Bistable Multivibrator.

NOTES:

#### 5.0 DESIGN AIDS

# 5.1 Microchip Advanced Part Selector (MAPS)

MAPS is a software tool that helps semiconductor professionals efficiently identify Microchip devices that fit a particular design requirement.

Available at no cost from the Microchip website at www.microchip.com/maps, the MAPS is an overall selection tool for Microchip's product portfolio that includes Analog, Memory, MCUs and DSCs. Using this tool you can define a filter to sort features for a parametric search of devices and export side-by-side technical comparison reports. Helpful links are also provided for data sheets, purchase and sampling of Microchip parts.

#### 5.2 Analog Demonstration and Evaluation Boards

Microchip offers a broad spectrum of Analog Demonstration and Evaluation Boards that are designed to help you achieve faster time to market.

For a listing of these boards, and their corresponding user's guides and technical information, visit the Microchip website at www.microchip.com/analogtools. Three of our boards that are especially useful are:

- 8-Pin SOIC/MSOP/TSSOP/DIP Evaluation Board, P/N SOIC8EV
- 14-Pin SOIC/TSSOP/DIP Evaluation Board, P/N SOIC14EV
- 5/6-Pin SOT23 Evaluation Board, P/N VSUPEV2

#### 5.3 Application Notes

The following Microchip Application Note is available on the Microchip website at www.microchip.com and is recommended as a supplemental reference resource:

 AN895 – "Oscillator Circuits For RTD Temperature Sensors" (DS00895).

#### 5.4 SPICE Macro Model

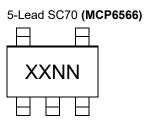
The latest SPICE macro model for the MCP6566/7/9 op amp is available on the Microchip website at www.microchip.com. The model was written and tested in the official Cadence<sup>®</sup> (OrCAD<sup>TM</sup>) PSpice<sup>®</sup>. For the other simulators, translation may be required.

The model covers a wide aspect of the comparator's electrical specifications. Not only does the model cover voltage, current and resistance of the comparator, but it also covers the temperature and noise effects on the behavior of the comparator. The model has not been verified outside of the specification range listed in the comparator data sheet. The model behaviors under these conditions cannot ensure it will match the actual comparator performance. Moreover, the model is intended to be an initial design tool. Bench testing is a very important part of any design and cannot be replaced with simulations. Also, simulation results using this macro model need to be validated by comparing them to the data sheet specifications and characteristic curves.

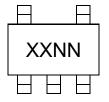
NOTES:

### 6.0 PACKAGING INFORMATION

#### 6.1 Package Marking Information



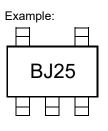
#### 5-Lead SOT-23 (MCP6566, MCP6566R)

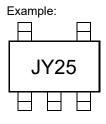


8-Lead MSOP (MCP6567)

Device	Code
MCP6566T	JYNN
MCP6566RT	JZNN
MCP6566UT	WLNN
Notes Annline to	

**Note:** Applies to 5-Lead SOT-23.





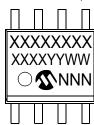


Example:



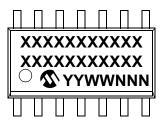
Legend	: XXX Y YY WW NNN @3 *	Customer-specific information Year code (last digit of calendar year) Year code (last 2 digits of calendar year) Week code (week of January 1 is week '01') Alphanumeric traceability code Pb-free JEDEC designator for Matte Tin (Sn) This package is Pb-free. The Pb-free JEDEC designator ((e3)) can be found on the outer packaging for this package.
	be carrie	nt the full Microchip part number cannot be marked on one line, it will d over to the next line, thus limiting the number of available s for customer-specific information.

8-Lead SOIC (150 mil) (MCP6567)

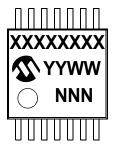


### Package Marking Information (Continued)

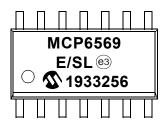
14-Lead SOIC (150 mil) (MCP6569)



14-Lead TSSOP (MCP6569)



Example:

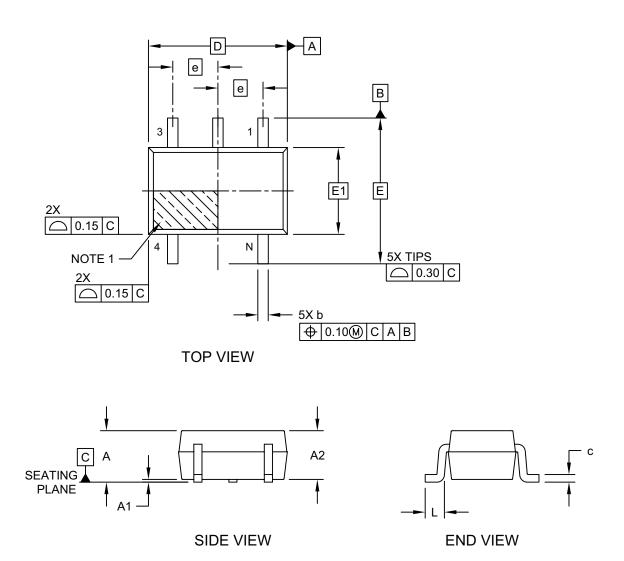


Example:



### 5-Lead Plastic Small Outline Transistor (LT) [SC70]

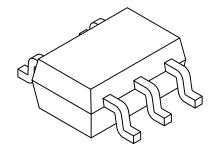
**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



Microchip Technology Drawing C04-061-LT Rev E Sheet 1 of 2

#### 5-Lead Plastic Small Outline Transistor (LT) [SC70]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



	MILLIMETERS					
Dimension	Dimension Limits					
Number of Pins	N		5			
Pitch	е		0.65 BSC			
Overall Height	Α	0.80 - 1.10				
Standoff	A1	0.00	-	0.10		
Molded Package Thickness	A2	0.80	-	1.00		
Overall Length	D	2.00 BSC				
Overall Width	E		2.10 BSC			
Molded Package Width	E1		1.25 BSC			
Terminal Width	b	0.15	-	0.40		
Terminal Length	L	0.10	0.20	0.46		
Lead Thickness	С	0.08	-	0.26		

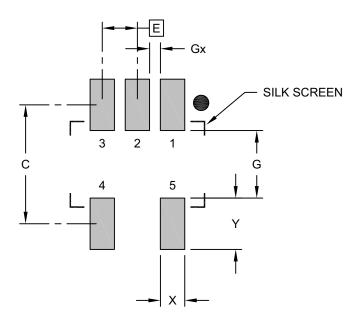
#### Notes:

- 1. Pin 1 visual index feature may vary, but must be located within the hatched area.
- 2. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or
- protrusions shall not exceed 0.15mm per side. 3. Dimensioning and tolerancing per ASME Y14.5M
  - BSC: Basic Dimension. Theoretically exact value shown without tolerances. REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing C04-061-LT Rev E Sheet 2 of 2

# 5-Lead Plastic Small Outline Transistor (LT) [SC70]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



#### RECOMMENDED LAND PATTERN

	Units	Ν	<b>/ILLIMETER</b>	S
Dimension	Limits	MIN	NOM	MAX
Contact Pitch	E		0.65 BSC	
Contact Pad Spacing	С		2.20	
Contact Pad Width	Х			0.45
Contact Pad Length				0.95
Distance Between Pads	G	1.25		
Distance Between Pads	Gx	0.20		

Notes:

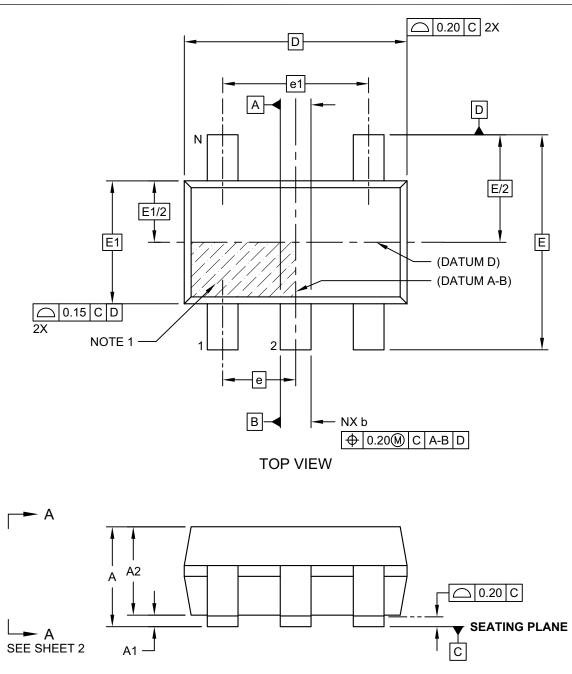
1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2061-LT Rev E

### 5-Lead Plastic Small Outline Transistor (OT) [SOT23]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging

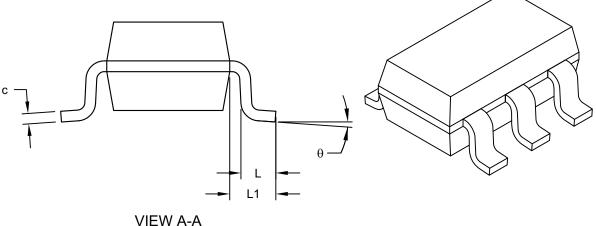


SIDE VIEW

Microchip Technology Drawing C04-091-OT Rev F Sheet 1 of 2

#### 5-Lead Plastic Small Outline Transistor (OT) [SOT23]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging





	Ν	ILLIMETER	S		
Dimension	Limits	MIN	NOM	MAX	
Number of Pins	Ν		5		
Pitch	е		0.95 BSC		
Outside lead pitch	e1		1.90 BSC		
Overall Height	Α	0.90	-	1.45	
Molded Package Thickness	A2	0.89	-	1.30	
Standoff	A1	-	-	0.15	
Overall Width	E	2.80 BSC			
Molded Package Width	E1	1.60 BSC			
Overall Length	D		2.90 BSC		
Foot Length	L	0.30	-	0.60	
Footprint	L1	0.60 REF			
Foot Angle	ø	0°	-	10°	
Lead Thickness	С	0.08	-	0.26	
Lead Width	b	0.20	-	0.51	

Notes:

1. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.25mm per side.

2. Dimensioning and tolerancing per ASME Y14.5M

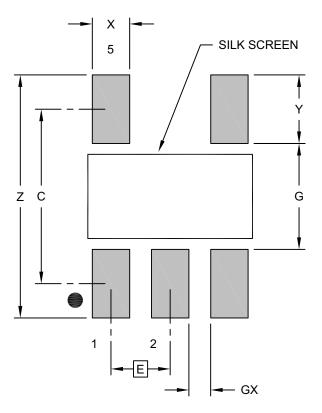
BSC: Basic Dimension. Theoretically exact value shown without tolerances.

REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing C04-091-OT Rev F Sheet 2 of 2

### 5-Lead Plastic Small Outline Transistor (OT) [SOT23]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



#### RECOMMENDED LAND PATTERN

	Units	MILLIMETERS			
Dimension	Limits	MIN	NOM	MAX	
Contact Pitch	E		0.95 BSC		
Contact Pad Spacing	С		2.80		
Contact Pad Width (X5) X				0.60	
Contact Pad Length (X5)	Y			1.10	
Distance Between Pads	G	1.70			
Distance Between Pads	GX	0.35			
Overall Width	Z			3.90	

Notes:

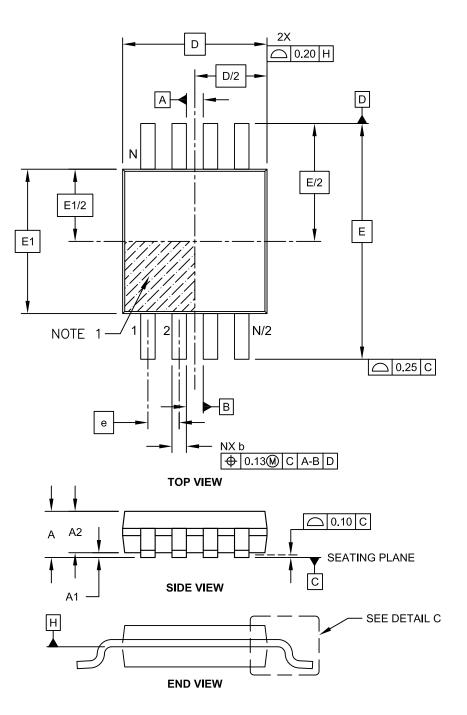
1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2091-OT Rev F

#### 8-Lead Plastic Micro Small Outline Package (MS) [MSOP]

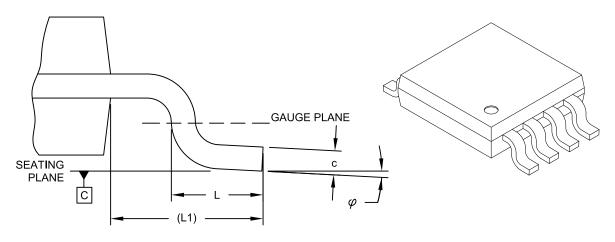
**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



Microchip Technology Drawing C04-111C Sheet 1 of 2

#### 8-Lead Plastic Micro Small Outline Package (MS) [MSOP]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



DETAIL C

Units		MILLIMETERS		
Dimension Limits		MIN	NOM	MAX
Number of Pins	N		8	
Pitch	е	0.65 BSC		
Overall Height	A	-	-	1.10
Molded Package Thickness	A2	0.75	0.85	0.95
Standoff	A1	0.00	-	0.15
Overall Width	E	4.90 BSC		
Molded Package Width	E1	3.00 BSC		
Overall Length	D	3.00 BSC		
Foot Length	L	0.40	0.60	0.80
Footprint	L1	0.95 REF		
Foot Angle	φ	0°	-	8°
Lead Thickness	С	0.08	-	0.23
Lead Width	b	0.22	-	0.40

#### Notes:

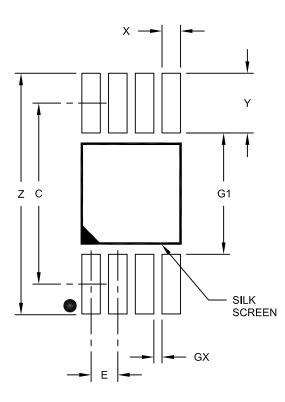
1. Pin 1 visual index feature may vary, but must be located within the hatched area.

- Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.15mm per side.
  Dimensioning and tolerancing per ASME Y14.5M.
  - Dimensioning and tolerancing per ASME Y14.5M. BSC: Basic Dimension. Theoretically exact value shown without tolerances. REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing C04-111C Sheet 2 of 2

#### 8-Lead Plastic Micro Small Outline Package (MS) [MSOP]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



#### RECOMMENDED LAND PATTERN

	Units		MILLIMETERS		
Dimensio	Dimension Limits		NOM	MAX	
Contact Pitch	Е	0.65 BSC			
Contact Pad Spacing	С		4.40		
Overall Width	Z			5.85	
Contact Pad Width (X8)	X1		0.45		
Contact Pad Length (X8)	Y1			1.45	
Distance Between Pads	G1	2.95			
Distance Between Pads	GX	0.20			

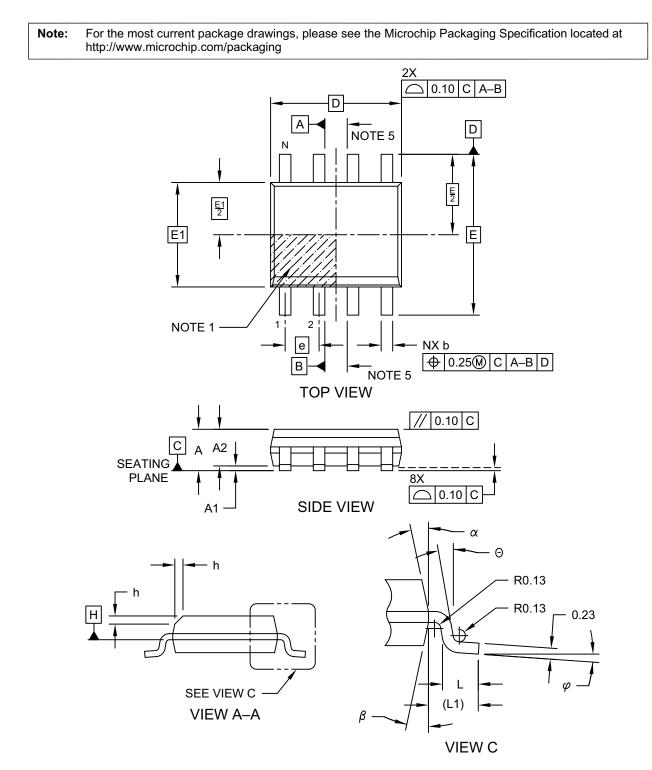
Notes:

1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2111A

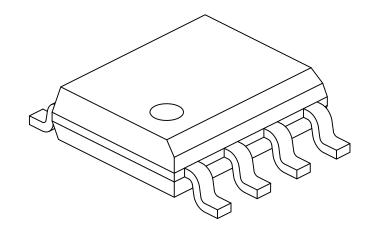
### 8-Lead Plastic Small Outline (SN) - Narrow, 3.90 mm (.150 In.) Body [SOIC]



Microchip Technology Drawing No. C04-057-SN Rev E Sheet 1 of 2

#### 8-Lead Plastic Small Outline (SN) - Narrow, 3.90 mm (.150 In.) Body [SOIC]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



	MILLIMETERS			
Dimension Limits		MIN	NOM	MAX
Number of Pins	N		8	
Pitch	е		1.27 BSC	
Overall Height	Α	-	-	1.75
Molded Package Thickness	A2	1.25	-	-
Standoff §	A1	0.10	-	0.25
Overall Width	E	6.00 BSC		
Molded Package Width	E1	3.90 BSC		
Overall Length	D	4.90 BSC		
Chamfer (Optional)	h	0.25	-	0.50
Foot Length	L	0.40 - 1.27		
Footprint	L1	1.04 REF		
Foot Angle	φ	0° - 8°		
Lead Thickness	С	0.17 - 0.25		0.25
Lead Width	b	0.31 - 0.51		
Mold Draft Angle Top	α	5° - 15°		
Mold Draft Angle Bottom	β	5° - 15°		

Notes:

1. Pin 1 visual index feature may vary, but must be located within the hatched area.

2. § Significant Characteristic

- 3. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.15mm per side.
- 4. Dimensioning and tolerancing per ASME Y14.5M
  - BSC: Basic Dimension. Theoretically exact value shown without tolerances.

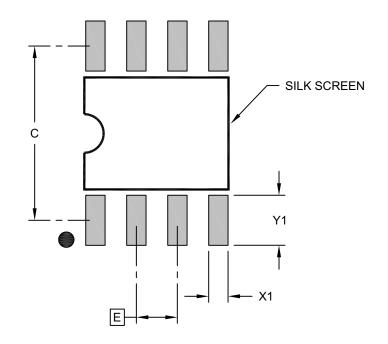
REF: Reference Dimension, usually without tolerance, for information purposes only.

5. Datums A & B to be determined at Datum H.

Microchip Technology Drawing No. C04-057-SN Rev E Sheet 2 of 2

#### 8-Lead Plastic Small Outline (SN) - Narrow, 3.90 mm Body [SOIC]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



#### RECOMMENDED LAND PATTERN

Units		MILLIMETERS			
Dimension Limits		MIN	NOM	MAX	
Contact Pitch	E		1.27 BSC		
Contact Pad Spacing	С		5.40		
Contact Pad Width (X8)	X1			0.60	
Contact Pad Length (X8)	Y1			1.55	

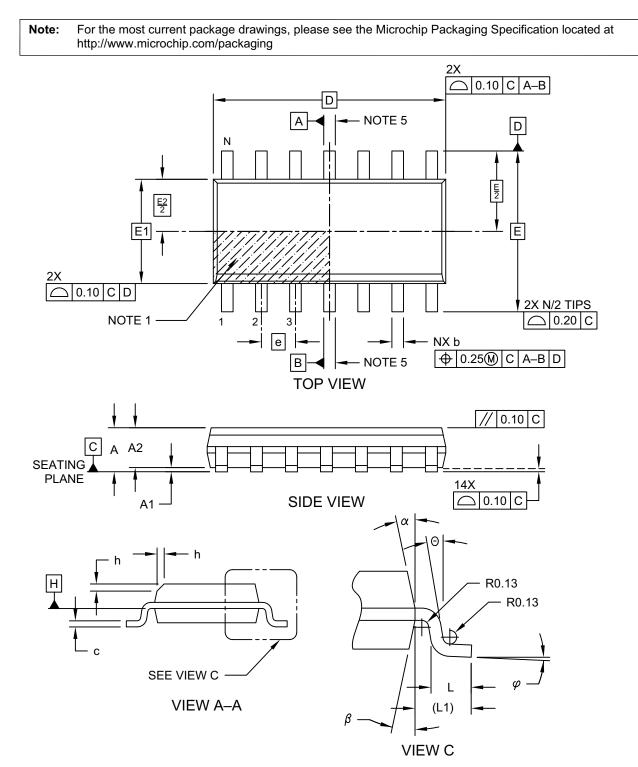
Notes:

1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing C04-2057-SN Rev E

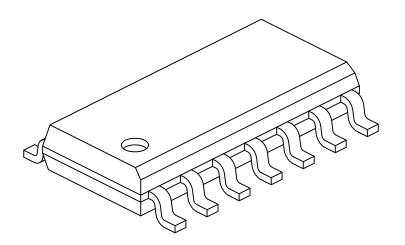
## 14-Lead Plastic Small Outline (SL) - Narrow, 3.90 mm Body [SOIC]



Microchip Technology Drawing No. C04-065-SL Rev D Sheet 1 of 2

#### 14-Lead Plastic Small Outline (SL) - Narrow, 3.90 mm Body [SOIC]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



	MILLIMETERS			
Dimension L		MIN	NOM	MAX
Number of Pins	N	14		
Pitch	е		1.27 BSC	
Overall Height	Α	-	-	1.75
Molded Package Thickness	A2	1.25	-	-
Standoff §	A1	0.10 - 0.25		
Overall Width	E	6.00 BSC		
Molded Package Width	E1	3.90 BSC		
Overall Length	D	8.65 BSC		
Chamfer (Optional)	h	0.25 - 0.50		
Foot Length	L	0.40 - 1.2		1.27
Footprint	L1	1.04 REF		
Lead Angle	Θ	0°		
Foot Angle	φ	0° - 8°		
Lead Thickness	С	0.10 - 0.25		
Lead Width	b	0.31	-	0.51
Mold Draft Angle Top	α	5°	-	15°
Mold Draft Angle Bottom	β	5° - 15°		

Notes:

- 1. Pin 1 visual index feature may vary, but must be located within the hatched area.
- 2. § Significant Characteristic
- Dimension D does not include mold flash, protrusions or gate burrs, which shall not exceed 0.15 mm per end. Dimension E1 does not include interlead flash or protrusion, which shall not exceed 0.25 mm per side.
- Dimensioning and tolerancing per ASME Y14.5M BSC: Basic Dimension. Theoretically exact value shown without tolerances.

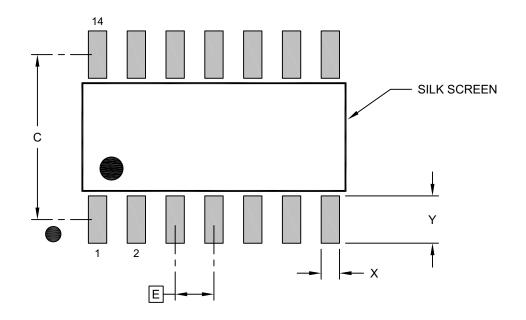
REF: Reference Dimension, usually without tolerance, for information purposes only.

5. Datums A & B to be determined at Datum H.

Microchip Technology Drawing No. C04-065-SL Rev D Sheet 2 of 2

#### 14-Lead Plastic Small Outline (SL) - Narrow, 3.90 mm Body [SOIC]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



#### RECOMMENDED LAND PATTERN

Units		MILLIMETERS			
Dimension Limits		MIN	NOM	MAX	
Contact Pitch	E		1.27 BSC		
Contact Pad Spacing	С		5.40		
Contact Pad Width (X14)	Х			0.60	
Contact Pad Length (X14)	Y			1.55	

Notes:

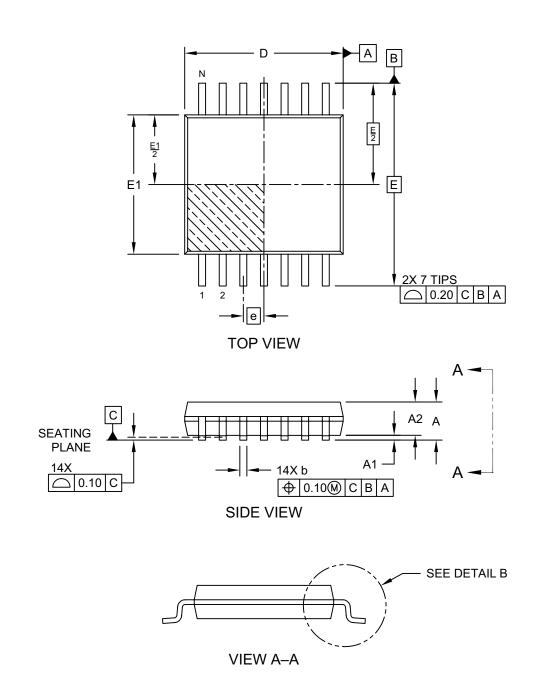
1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2065-SL Rev D

## 14Lead Thin Shrink Small Outline Package [ST] 4.4 mm Body [TSSOP]

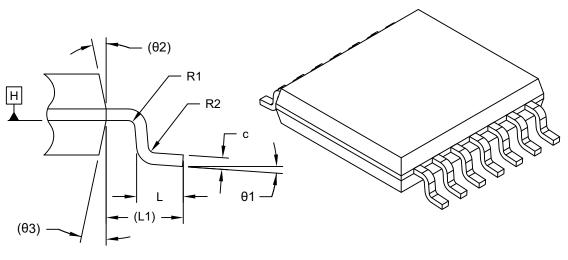
**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



Microchip Technology Drawing C04-087 Rev D Sheet 1 of 2

#### 14Lead Thin Shrink Small Outline Package [ST] 4.4 mm Body [TSSOP]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



	Units			MILLIMETERS			
	<b>Dimension Limits</b>	Limits MIN NOM N					
Number of Terminals	N	14					
Pitch	е	0.65 BSC					
Overall Height	А	-	-	1.20			
Standoff	A1	0.05	-	0.15			
Molded Package Thickness	A2	0.80	1.00	1.05			
Overall Length	D	4.90	5.00	5.10			
Overall Width	E	6.40 BSC					
Molded Package Width	E1	4.30 4.40 4		4.50			
Terminal Width	b	0.19 – 0		0.30			
Terminal Thickness	С	0.09 – 0		0.20			
Terminal Length	L	0.45	0.60	0.75			
Footprint	L1		1.00 REF				
Lead Bend Radius	R1	0.09 –		-			
Lead Bend Radius	R2	0.09 –		_			
Foot Angle	θ1	0°	-	8°			
Mold Draft Angle	θ2	– 12° REF –					
Mold Draft Angle	θ3	θ3 – 12° REF –					

Notes:

1. Pin 1 visual index feature may vary, but must be located within the hatched area.

2. Dimensioning and tolerancing per ASME Y14.5M

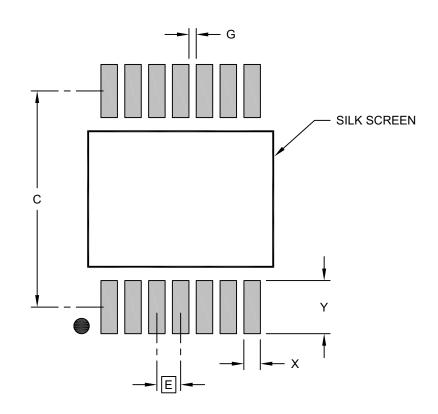
BSC: Basic Dimension. Theoretically exact value shown without tolerances.

REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing C04-087 Rev D Sheet 2 of 2

## 14Lead Thin Shrink Small Outline Package [ST] 4.4 mm Body [TSSOP]

**Note:** For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



#### **RECOMMENDED LAND PATTERN**

	Units	MILLIMETERS			
Dimension	Dimension Limits		NOM	MAX	
Contact Pitch	E	0.65 BSC			
Contact Pad Spacing	С	5.90			
Contact Pad Width (Xnn)	Х			0.45	
Contact Pad Length (Xnn)	Y			1.45	
Contact Pad to Contact Pad (Xnn)	G	0.20			

Notes:

1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing C04-2087 Rev D

### APPENDIX A: REVISION HISTORY

#### **Revision G (March 2020)**

The following is the list of modifications:

 Updated package drawings for the 5-Lead SC70 and 14-lead TSSOP packages in Section 6.0 "Packaging Information".

#### **Revision F (August 2019)**

The following is the list of modifications:

1. Updated Section 6.0 "Packaging Information".

#### **Revision E (September 2014)**

The following is the list of modifications:

- 1. Added SPICE Macro Model in the Related Device features section.
- 2. Updated Temperature Specifications table.
- 3. Corrected pin table in Section 3.0 "Pin Descriptions".
- 4. Added new Section 5.4, SPICE Macro Model.

#### **Revision D (February 2013)**

The following is the list of modifications:

1. Added the Analog Input (V<sub>IN</sub>) parameter in Section 1.0 "Electrical Characteristics".

#### **Revision C (February 2011)**

The following is the list of modifications:

1. Replaced the MCP5468 package name with the correct MCP6567 package name on page 1 and in Table 3-1.

#### **Revision B (August 2009)**

The following is the list of modifications:

- 1. Added MCP6566U throughout the document.
- 2. Updated package outline drawings.

#### **Revision A (March 2009)**

• Original Release of this Document.

# MCP6566/6R/6U/7/9

NOTES:

### **PRODUCT IDENTIFICATION SYSTEM**

To order or obtain information, e.g., on pricing or delivery, refer to the factory or the listed sales office.

PART NO. – X /XX		Ex	Examples:			
Device 1	Temperature Package Range	a) b)	MCP6566T-E/LT: MCP6566T-E/OT:	Tape and Reel, Extended Temperature, 5-Lead SC70 Package. Tape and Reel,		
Device:	MCP6566T: Single Comparator (Tape and Reel) (SC70, SOT-23)			Extended Temperature, 5-Lead SOT-23 Package.		
	MCP6566RT: Single Comparator (Tape and Reel) (SOT-23 only) MCP6566UT: Single Comparator (Tape and Reel) (SOT-23 only)	a)	MCP6566RT-E/OT:	Tape and Reel, Extended Temperature, 5-Lead SOT-23 Package.		
	MCP6567: Dual Comparator MCP6567T: Dual Comparator (Tape and Reel) MCP6569: Quad Comparator MCP6569T: Quad Comparator (Tape and Reel)	a)	MCP6566UT-E/OT:	Tape and Reel, Extended Temperature, 5-Lead SOT-23 Package.		
Temperature	$E = -40^{\circ}C \text{ to } +125^{\circ}C$	a)	MCP6567-E/MS:	Extended Temperature, 8-Lead MSOP Package.		
Range:		b)	MCP6567-E/SN:	Extended Temperature, 8-Lead SOIC Package.		
Package:	LT = Plastic Small Outline Transistor (SC70), 5-Lead OT = Plastic Small Outline Transistor (SOT-23), 5-Lead MS = Plastic Micro Small Outline Transistor, 8-Lead SN = Plastic Small Outline Transistor, 8-Lead ST = Plastic Thin Shrink Small Outline Transistor, 14-Lead	a) b)	MCP6569T-E/SL: MCP6569T-E/ST:	Tape and Reel, Extended Temperature, 14-Lead SOIC Package. Tape and Reel,		
	SL = Plastic Small Outline Transistor, 14-Lead			Extended Temperature, 14-Lead TSSOP Package.		

# MCP6566/6R/6U/7/9

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